



## 1. Description

SS029N10MS, the N-channel Enhanced Power MOSFETs, is obtained by advanced double trench technology which reduce the conduction loss, improve switching performance and enhance the avalanche energy. This is suitable device for BMS and high current switching applications.

### KEY CHARACTERISTICS

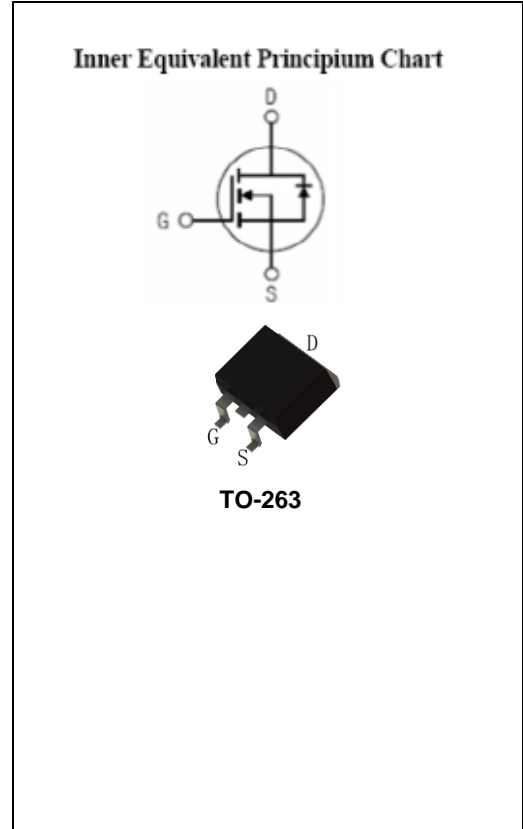
Parameter	Value	Unit
V <sub>DSS</sub>	100	V
I <sub>D</sub>	180	A
R <sub>DS(on).typ</sub>	2.5	mΩ

### FEATURES

- Fast Switching
- Low On-Resistance (  $R_{DS(on)} \leq 2.9m\Omega$  )
- Low Gate Charge
- Low Reverse transfer capacitances
- High avalanche ruggedness
- RoHS product

### APPLICATIONS

- BMS
- High current switching applications
- Synchronous rectification



### ORDERING INFORMATION

Ordering Codes	Package	Product Code	Packing
SS029N10MS	TO-263	SS029N10MS	Reel